

(54) MASKS FOR USE IN OPTICAL LITHOGRAPHY BELOW 180 NM

(57) ABSTRACT

A mask for use on a layer of imaging material which is located on at least a portion of one surface of a substrate in a lithography process in accordance with one embodiment of the present invention includes a layer of a masking material which has an optical density of at least 4.0 for wavelengths at or below about 180 nm and a thickness of less than about 1000 angstroms. Materials, such as tungsten and amorphous silicon, can be used for the mask.